

RJK0366DPA

Silicon N Channel Power MOS FET Power Switching

REJ03G1656-0600 Rev.6.00 Aug 05, 2008

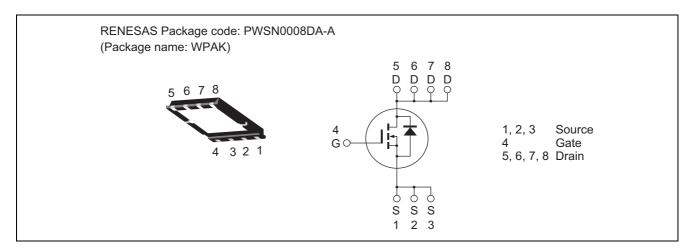
Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 8.5 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$

• Pb-free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	25	A
Drain peak current	I _{D(pulse)} Note1	100	A
Body-drain diode reverse drain current	I _{DR}	25	A
Avalanche current	I _{AP} Note 2	11	A
Avalanche energy	E _{AR} Note 2	12.1	mJ
Channel dissipation	Pch Note3	30	W
Channel to case thermal resistance	θch-c Note3	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \mu s$, duty cycle $\le 1\%$

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. $Tc = 25^{\circ}C$

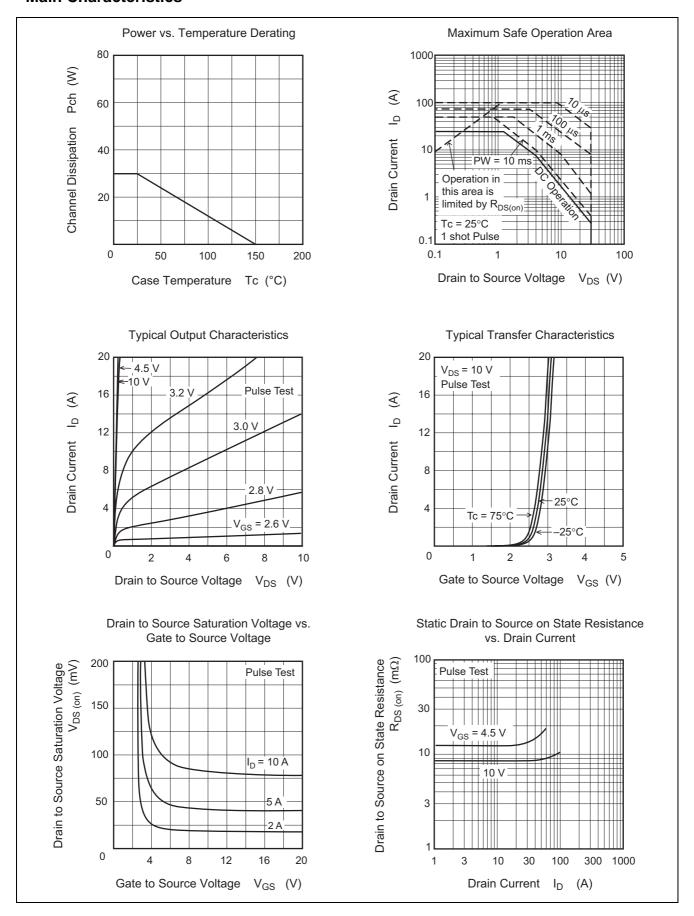
Electrical Characteristics

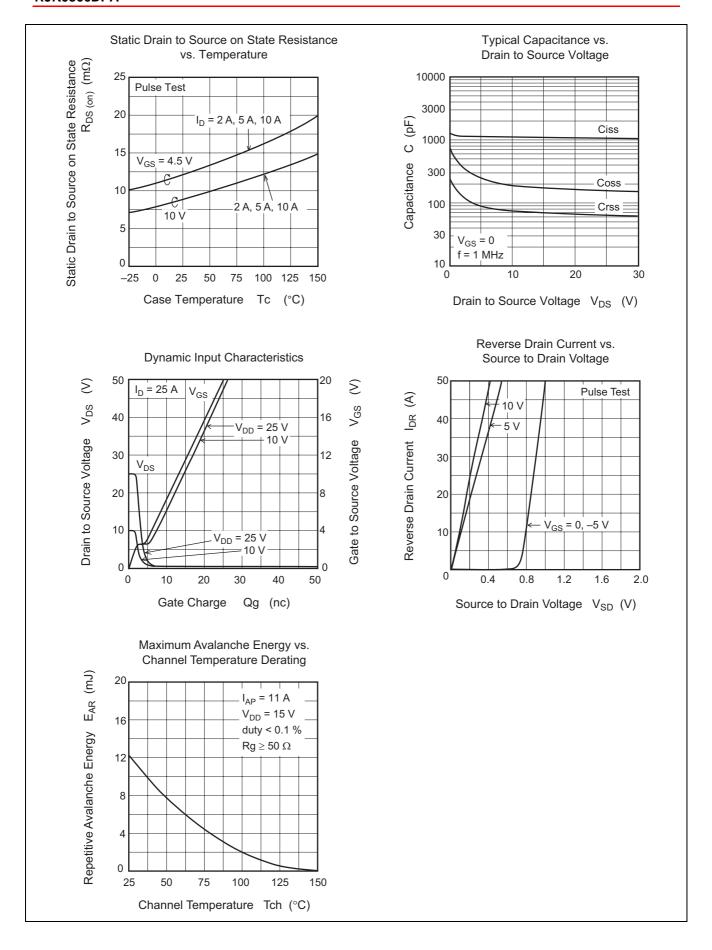
 $(Ta = 25^{\circ}C)$

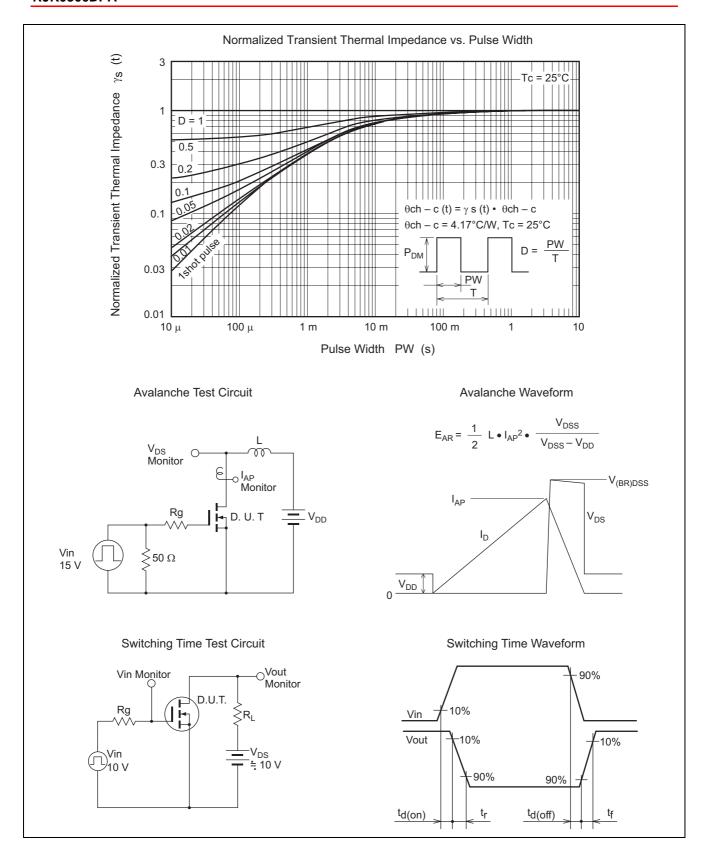
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	± 0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}		_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	8.5	11.1	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	12.0	16.8	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	_	50	_	S	$I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1010	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	190	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	75	_	pF	f = 1 MHz
Gate Resistance	Rg	_	1.1	_	Ω	
Total gate charge	Qg	_	6.8	_	nC	V _{DD} = 10 V
Gate to source charge	Qgs	_	2.5	_	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Qgd	_	1.5	_	nC	I _D = 12.5 A
Turn-on delay time	t _{d(on)}	_	5.0	_	ns	$V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A}$
Rise time	t _r	_	3.6	_	ns	V _{DD} ≅ 10 V
Turn-off delay time	t _{d(off)}	_	33	_	ns	$R_L = 0.8 \Omega$
Fall time	t _f	_	4.2	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.89	1.16	V	$I_F = 25 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery	t _{rr}	_	20	_	ns	I _F =25 A, V _{GS} = 0
time						$di_F/dt = 100 A/ \mu s$

Notes: 4. Pulse test

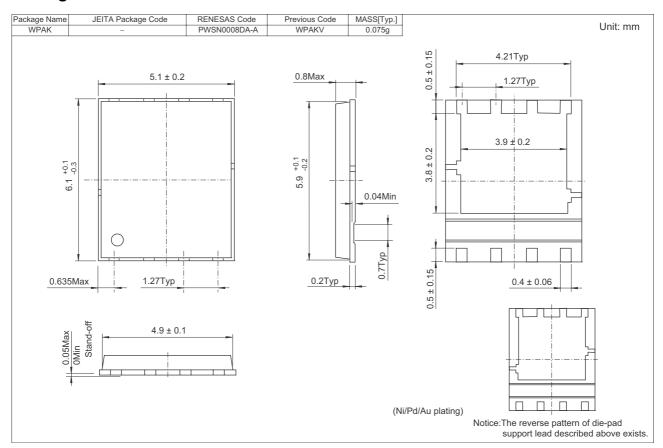
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0366DPA-00-J0	2500 pcs	Taping

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